

## N Channel Enhancement

- High speed switchin



(Tc = 25°C unless otherwise specified)

V



$Q_{gs}$	Gate source charge	-	12	-	nC	$V_{DS} = 500V, V_{GS} = -4/+18V$ $I_D = 22A$	Fig.12
$Q_{gd}$	Gate drain charge	-	12	-			
$Q_g$	Gate charge	-	38	-			

( $T_c = 25^\circ C$  unless otherwise specified, the data comes from TO-247-4L)

$E_{on}$	Turn on switching energy	-	85	-	$\mu J$	$V_{DS} = 500V, V_{GS} = -4/+18V$ $I_D = 22A, R_g = 2.5$ $L = 120\mu H$	
$E_{off}$	Turn off switching energy	-	31	-			
$t_{d on}$	Turn on delay time	-	10.7	-	ns		
$t_r$	Rise time	-	11.6	-			
$t_{d off}$	Turn off delay time	-	21	-			
$t_f$	Fall time	-	9.5	-			

(The data comes from TO-247-4L)

$V_{SD}$	Diode forward voltage	-	3.7	-	V	$V_{GS} = -4V, I_{SD} = 11A$	Fig.8,9, 10
		-	3.2	-	V	$V_{GS} = -4V, I_{SD} = 11A$ $T_J = 175^\circ C$	
$I_S$	Continuous diode forward current	-	54	-	A	$V_{GS} = -4V, T_c = 25^\circ C$	Note2
$t_{rr}$	Reverse recovery time	-	25	-	ns	$V_R = 500V, V_{GS} = -4V$	
$Q_{rr}$	Reverse recovery charge	-	246	-	nC	$I_{SD} = 22A$	
$I_{rrm}$	Peak reverse recovery current	-	17	-	A	$di/dt = 2111A/\mu s$ $T_J = 175^\circ C$	

Note 2: When using SiC Body Diode the maximum recommended  $V_{GS} = -4 V$

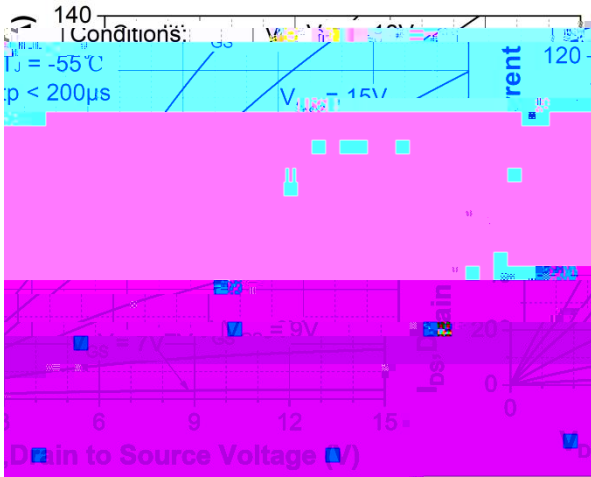


Figure 1. Output characteristics  $T_J = -55\text{ }^\circ\text{C}$

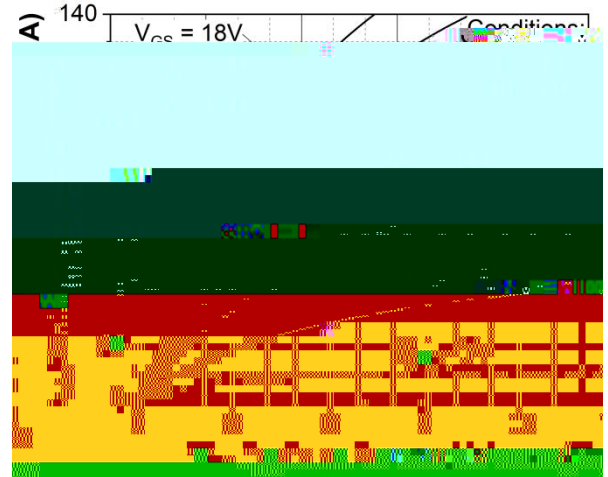


Figure 2. Output characteristics  $T_J = 25\text{ }^\circ\text{C}$

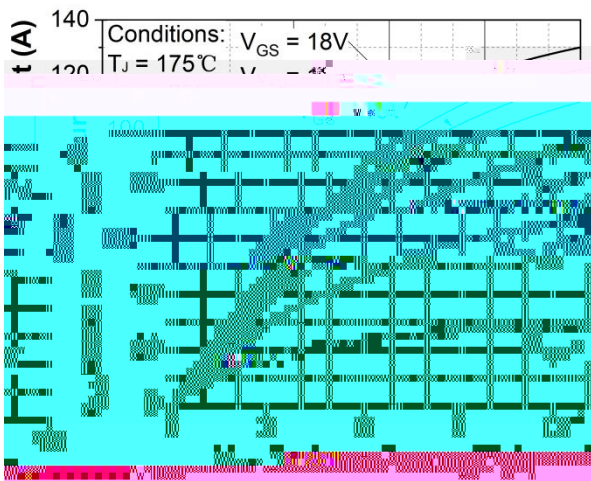


Figure 3. Output characteristics  $T_J = 175\text{ }^\circ\text{C}$



Figure 4. Normalized on-resistance vs. temperature

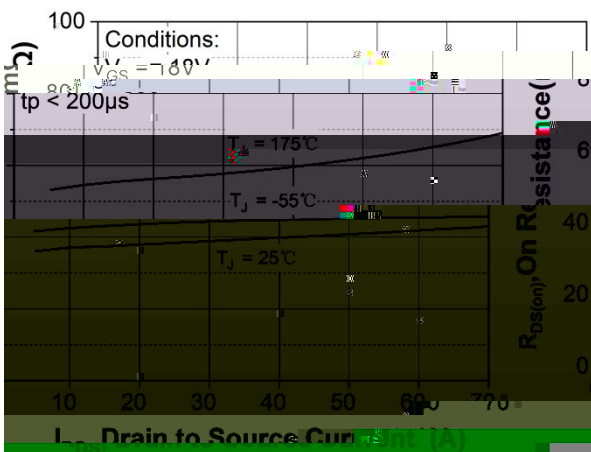


Figure 5. On-resistance vs. drain current for various temperatures

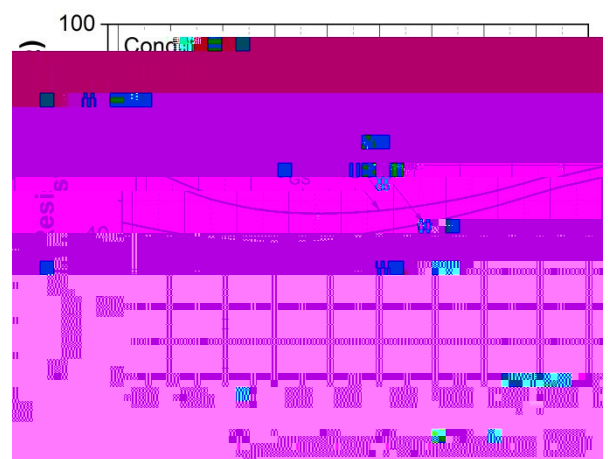


Figure 6. On-resistance vs. temperature for various gate voltages

Figure 7. Transfer characteristic for various junction temperatures

Figure 8. Body diode characteristic at  $T_J = -55\text{ }^\circ\text{C}$

Figure 9. Body diode characteristic at  $T_J = 25\text{ }^\circ\text{C}$

Figure 10.





Die size	W x L	2.800*3.400	mm
Gate pad size	W x L	0.800*0.800	mm
Die thickness		175	μm
Top side	source gate		

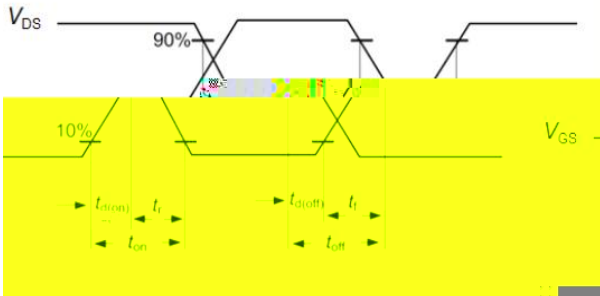


Figure A. Definition of switching times

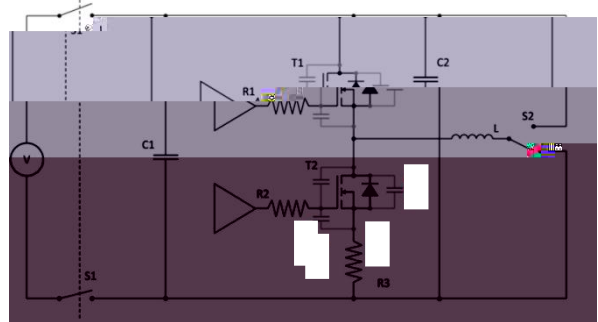


Figure B. Dynamic test circuit

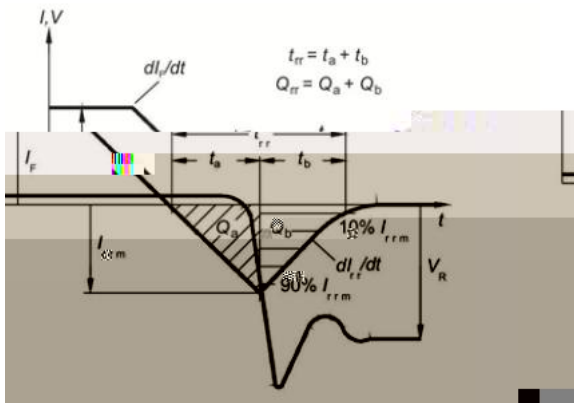


Figure C. Definition of body diode switching characteristics

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